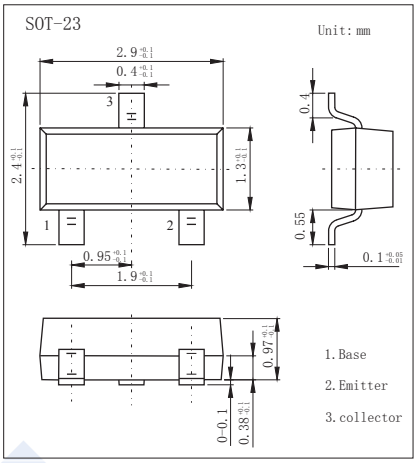
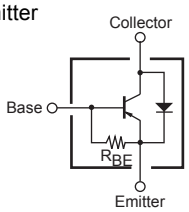
PNP Transistors

2SB1527



■ Features

- Large current capatance
- Low collector-emitter saturation voltage
- Contains a bias resisror between base and emitter



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-20	V
Collector - Emitter Voltage	V_{CEO}	-15	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-0.8	A
Collector Current - Pulse	I_{CP}	-2	
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	150	℃
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= -100 uA, I_E=0	-20			V
Collector- emitter breakdown voltage	V_{CEO}	I_C= -10 mA, R_{BE}=∞	-15			
Emitter - base breakdown voltage	V_{EBO}	I_E= -100 uA, I_C=0	-5			
Collector-base cut-off current	I_{CBO}	V_{CB}= -15V , I_E=0			-1	uA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500 mA, I_B=-10 mA		-0.2	-0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	I_C=-500 mA, I_B=-10 mA		-0.95	-1.3	
DC current gain	h_{FE}	V_{CE}= -2V, I_C= -500 mA	70			
Diode forward voltage	V_F	I_F=0.5A			-1.5	V
Base - emitter resistance	R_{BE}			1		kΩ
Collector output capacitance	C_{ob}	V_{CB}= -10V, I_E= 0,f=1MHz		30		pF
Transition frequency	f_T	V_{CE}= -2V, I_C= -500 mA		250		MHz

■ Marking

Marking	NS

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■ Typical Characterisitics